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Application Serial No. 10/729,694
Reply to Office Action of November 22, 2006

PATENT
Docket No. CU-3477

Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

Listing of claims:

1. **(currently amended)** A method for fabricating a capacitor in a semiconductor device, the method comprising the steps of:

forming an interlayer insulating film on a semiconductor substrate, which includes a first contact hole exposing a portion of the substrate;

forming a storage node plug filling the first contact hole;

forming a first insulating film, a first silicon nitride film, and a second insulating film sequentially above the substrate inclusive of the storage node plug;

forming a second silicon nitride film at least on the interlayer insulating film, before forming the first insulating film **wherein the first and second silicon nitride films are substantially parallel to each other;**

forming a second contact hole that exposes the storage node plug by removing the second insulating film, the first silicon nitride film, and the first insulating film partly;

forming a recessed portion at side surfaces of the second contact hole and below the silicon nitride film by wet-etching the first insulating film remained in the second contact hole;

forming a storage node electrode of the capacitor, which is connected to the storage node plug, by filling the second contact hole inclusive of the recessed portion;

removing the remained second insulating film;

forming a dielectric film on the storage node electrode; and

forming a plate electrode on the dielectric film and the silicon nitride film.

2. **(canceled)**

3. **(original)** The method as claimed in claim 1, wherein the first insulating film has an etching rate faster than that of the first silicon nitride film.

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4. (original) The method as claimed in claim 3, wherein the first insulating film comprises a BSPG film.
5. (original) The method as claimed in claim 1, wherein the second insulating film is formed to a thickness of 10000 ~ 20000Å.
6. (original) The method as claimed in claim 1, wherein the second insulating film comprises a PSG film.
7. (original) The method as claimed in claim 1, wherein the recessed portion of the storage node electrode has a broader width than that of any other portion of the storage node electrode.